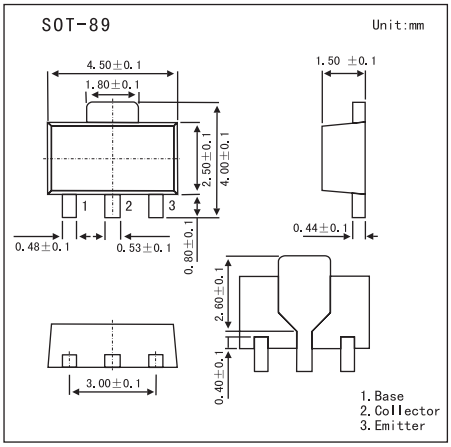
TY Semicondutor®

Product specification

2SC4543



■ Features

- High transition frequency fT
- Small collector output capacitance cob
- Wide current range.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	110	V
Collector-emitter voltage	V_{CER} *	100	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	3.5	V
Peak collector current	I_{CP}	300	mA
Collector current	I_C	150	mA
Collector power dissipation	P_C	1.0	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* R_{EB}=1.2KΩ

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CEO}	V_{CE} = 35 V, I_B = 0			10	μA
Collector-base voltage	V_{CBO}	I_C = 100 μA, I_E = 0	110			V
Collector-emitter voltage	V_{CER}	I_C = 500 μA, R_{BE} = 470Ω	100			V
Collector-emitter voltage	V_{CEO}	I_C = 1 mA, I_B = 0	50			V
Emitter-base voltage	V_{EBO}	I_E = 100 μA, I_C = 0	3.5			V
Forward current transfer ratio	h_{FE}	V_{CE} = 5 V, I_C = 100 mA	20			?
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 150 mA, I_B = 15 mA			0.5	V
Transition frequency	f_{T1}	V_{CB} = 10 V, I_E = -10 mA, f = 200 MHz		300		MHz
	f_{T2}	V_{CB} = 10 V, I_E = -110 mA, f = 200 MHz		350		MHz
Collector output capacitance	C_{ob}	V_{CB} = 30 V, I_E = 0, f = 1 MHz		3		pF

* R_{EB}=1.2KΩ

■ Marking

Marking	1F